

PATENT APPLICATION
Attorney Docket No.: 2000.010.00/US

PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT FORM PTO-1449 (Modified) (USE AS MANY SHEETS AS NECESSARY)				Application Number	
				Filing Date	
				First Named Inventor	Farid Nemati
				Art Unit	
				Examiner Name	
SHEET	1	OF	2	Attorney Docket Number	2000.010.00/US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. 1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number- Kind Code (if known)			
P D		US 6,229,161 ✓	05-08-01	Nemati et al.	
↑		US 6,448,586 ✓	09-10-02	Nemati et al.	
		US 6,462,359 ✓	10-08-02	Nemati et al.	
		US 6,528,356 ✓	03-04-03	Nemati et al.	
		US 5,448,104 ✓	09-05-95	Yallup	
		US-5,627,401 ✓	05-06-97	Yallup	
		US-4,965,872 ✓	10-23-90	Vasudev	
		US-6,492,662 ✓	12-10-02	Hsu, et al.	
		US-6,512,274 ✓	01-28-03	King, et al.	
		US-6,545,297 ✓	04-08-03	Noble, Jr., et al.	
		US-6,552,398 ✓	04-22-03	Hsu, et al.	
		US-6,583,452 ✓	06-24-03	Cho, et al.	
↓		US-6,611,452 ✓	08-26-03	Han	
P D		US-6,627,924 ✓	09-30-03	Hsu, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No. 1	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Ts
		Country Code 3- Number 4 - Kind Code 5 (if known)				

Examiner Signature	PHUC T. DANG	Date Considered	5/5/2005
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OTHER PRIOR ART – LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T2
PD ↑		FARID NEMATI et al., U.S. Pat. Appl. Ser. No. 10/706,162, filed Nov. 12, 2003, <i>Thyristor Circuit and Approach for Temperature Stability</i> , assigned to the assignee of the present application. C-028	
		F.NEMATI and J.D. PLUMMER, <i>A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device</i> , VLSI Technology Technical Digest, 1998.	
		F.NEMATI and J.D. PLUMMER, <i>A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-Scale Memories</i> , International Electron Device Meeting Technical Digest 1999.	
		NATIONAL SCIENTIFIC CORP., <i>TMOS Memory Cell, Breakthrough Technology in SRAM</i> , at http://www.nsclocators.com/images/pdf/IP_tm05-2003.PDF , 2003.	
PD ↓		R.COLIN JOHNSON, <i>Hybrid Tunnel Diodes Could Leapfrog Moore's Law</i> , EE Times, October 29, 2003, also at www.eetimes.com/at/news/OEG20031029S0015 .	

Examiner Signature	PHUC T. DANG	Date Considered	5/5/2005
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